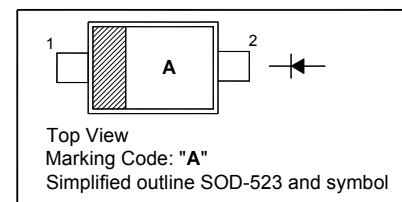


BAS216WT

Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



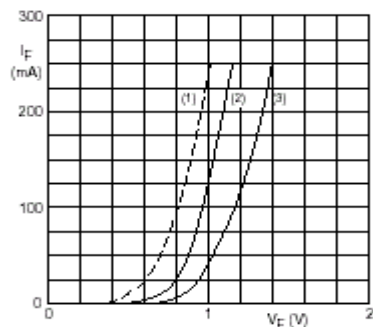
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ }\mu\text{s}$ 4	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ s}$ 0.5	
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

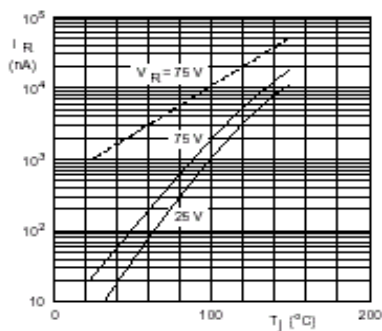
Parameter	Symbol	Max.	Unit			
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	715 855 1000 1250	mV			
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_J = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_J = 150\text{ }^\circ\text{C}$		I_R		30 1 30 50	nA μA μA μA	
Diode Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$				C_{tot}	1.5	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$				t_{rr}	4	ns

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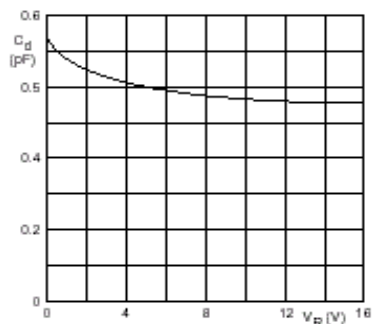
- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values.
- (2) $T_j = 25\text{ }^\circ\text{C}$; typical values.
- (3) $T_j = 25\text{ }^\circ\text{C}$; maximum values.

Forward current as a function of forward voltage.



Dotted line: maximum values.
 Solid line: typical values.

Reverse current as a function of junction temperature.



$f = 1\text{ MHz}$; $T_j = 25\text{ }^\circ\text{C}$.

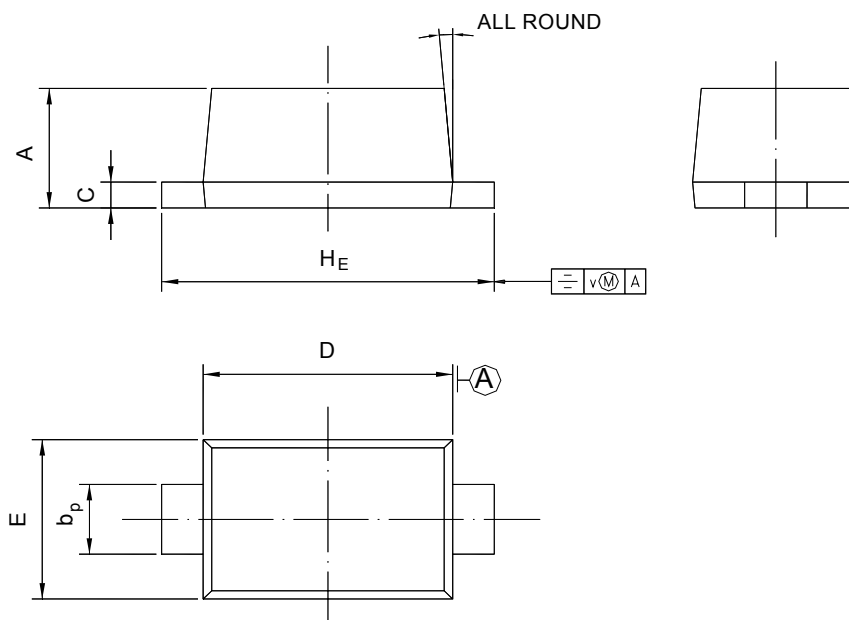
Diode capacitance as a function of reverse voltage; typical values.

BAS216WT

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	
mm	0.70	0.4	0.135	1.25	0.85	1.7	0.1	5°
	0.60	0.3	0.100	1.15	0.75	1.5		